CY7C1020CV33

512K (32K x 16) Static RAM

Features

- **Pin- and function-compatible with CY7C1020V33**
- **Temperature Ranges**
  - **— Commercial: 0°C to 70°C**
  - **— Industrial: –40°C to 85°C**
  - **— Automotive: –40°C to 125°C**
- **High speed**
  - **— t_{AA} = 10 ns**
- **CMOS for optimum speed/power**
- **Low active power**
  - **— 325 mW (max.)**
- **Automatic power-down when deselected**
- **Independent control of upper and lower bits**
- **Available in Pb-free and non Pb-free 44-pin TSOP II package**

Functional Description

The CY7C1020CV33 is a high-performance CMOS static RAM organized as 32,768 words by 16 bits. This device has an automatic power-down feature that significantly reduces power consumption when deselected.

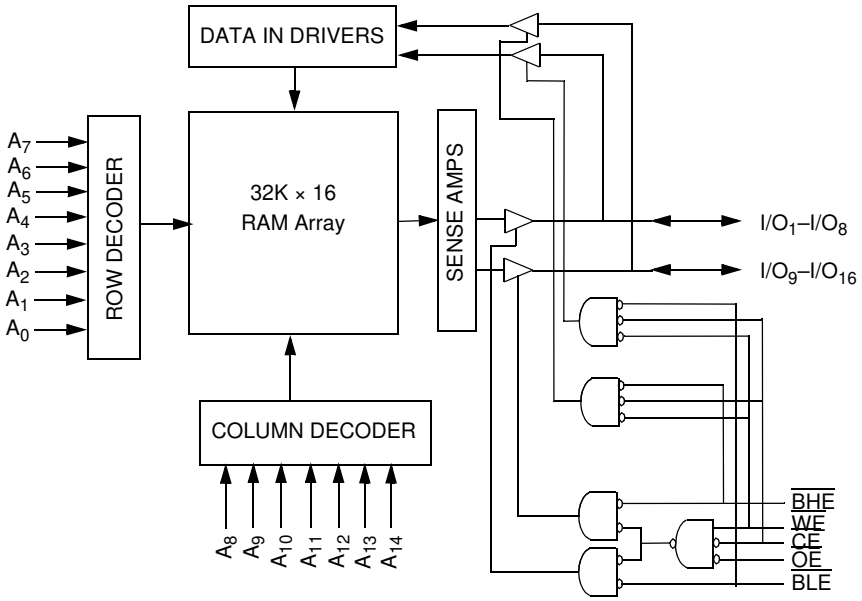
Writing to the device is accomplished by taking Chip Enable ($\overline{CE}$) and Write Enable ($\overline{WE}$) inputs LOW. If Byte Low Enable ($\overline{BLE}$) is LOW, then data from I/O pins (I/O_1 through I/O_8), is written into the location specified on the address pins (A_0 through A_{14}). If Byte High Enable ($\overline{BHE}$) is LOW, then data from I/O pins (I/O_9 through I/O_{16}) is written into the location specified on the address pins (A_0 through A_{14}).

Reading from the device is accomplished by taking Chip Enable ($\overline{CE}$) and Output Enable ($\overline{OE}$) LOW while forcing the Write Enable ($\overline{WE}$) HIGH. If Byte Low Enable ($\overline{BLE}$) is LOW, then data from the memory location specified by the address pins will appear on I/O_1 to I/O_8. If Byte High Enable ($\overline{BHE}$) is LOW, then data from memory will appear on I/O_9 to I/O_{16}. See the truth table at the back of this data sheet for a complete description of read and write modes.

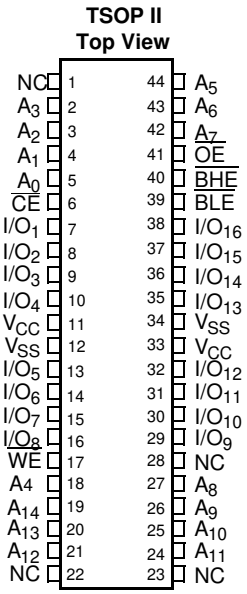
The input/output pins (I/O_1 through I/O_{16}) are placed in a high-impedance state when the device is deselected ($\overline{CE}$ HIGH), the outputs are disabled ($\overline{OE}$ HIGH), the $\overline{BHE}$ and $\overline{BLE}$ are disabled ($\overline{BHE}$, $\overline{BLE}$ HIGH), or during a write operation ($\overline{CE}$ LOW, and $\overline{WE}$ LOW).

The CY7C1020CV33 is available in standard 44-pin TSOP Type II package.

Logic Block Diagram



Pin Configuration[1]



Note:
1. NC pins are not connected on the die

Selection Guide

		-10	-12	-15	Unit
Maximum Access Time		10	12	15	ns
Maximum Operating Current	Com'l/Ind'l	90	85	80	mA
	Automotive	-	-	85	mA
Maximum CMOS Standby Current	Com'l/Ind'l	5	5	5	mA
	Automotive	-	-	10	mA

Pin Definitions

Pin Name	TSOP - Pin Number	I/O Type	Description
A_0–A_{14}	5, 4, 3, 2, 18, 44, 43, 42, 27, 26, 25, 24, 21, 20, 19	Input	**Address Inputs used to select one of the address locations**.
I/O_1–I/O_{16}	7-10, 13-16, 29-32, 35-38	Input/Output	**Bidirectional Data I/O lines**. Used as input or output lines depending on operation.
NC	1, 22, 23, 28	No Connect	**No Connects**. Not connected to the die.
$\overline{WE}$	17	Input/Control	**Write Enable Input, active LOW**. When selected LOW, a Write is conducted. When deselected HIGH, a Read is conducted.
$\overline{CE}$	6	Input/Control	**Chip Enable Input, active LOW**. When LOW, selects the chip. When HIGH, deselects the chip.
$\overline{BHE}$, $\overline{BLE}$	40, 39	Input/Control	**Byte Write Select Inputs, active LOW**. $\overline{BHE}$ controls I/O_{16}–I/O_9, $\overline{BLE}$ controls I/O_8–I/O_1.
$\overline{OE}$	41	Input/Control	**Output Enable, active LOW**. Controls the direction of the I/O pins. When LOW, the I/O pins are allowed to behave as outputs. When deasserted HIGH, I/O pins are tri-stated, and act as input data pins.
V_{SS}	12, 34	Ground	**Ground for the device**. Should be connected to ground of the system.
V_{CC}	11, 33	Power Supply	**Power Supply inputs to the device.**

Maximum Ratings

(Above which the useful life may be impaired. For user guidelines, not tested.)

Storage Temperature .....–65°C to +150°C

Ambient Temperature with Power Applied.....–55°C to +125°C

Supply Voltage on V_{CC} to Relative GND[1] .... –0.5V to +4.6V

DC Voltage Applied to Outputs in High-Z State[2] .....–0.5V to V_{CC} + 0.5V

DC Input Voltage[2].....–0.5V to V_{CC} + 0.5V

Current into Outputs (LOW)..... 20 mA

Static Discharge Voltage..... > 2001V (per MIL-STD-883, Method 3015)

Latch-up Current..... > 200 mA

Operating Range

Range	Ambient Temperature	V_{CC}
Commercial	0°C to +70°C	3.3V ± 10%
Industrial	–40°C to +85°C	3.3V ± 10%
Automotive	–40°C to +125°C	3.3V ± 10%

Electrical Characteristics Over the Operating Range

Parameter	Description	Test Conditions		-10		-12		-15		Unit
				Min.	Max.	Min.	Max.	Min.	Max.	
V_{OH}	Output HIGH Voltage	V_{CC} = Min., I_{OH} = –4.0 mA		2.4		2.4		2.4		V
V_{OL}	Output LOW Voltage	V_{CC} = Min., I_{OL} = 8.0 mA			0.4		0.4		0.4	V
V_{IH}	Input HIGH Voltage			2.0	V_{CC} + 0.3	2.0	V_{CC} + 0.3	2.0	V_{CC} + 0.3	V
V_{IL}	Input LOW Voltage[2]			–0.3	0.8	–0.3	0.8	–0.3	0.8	V
I_{IX}	Input Leakage Current	GND ≤ V_I ≤ V_{CC}	Com'l/Ind'l	–1	+1	–1	+1	–1	+1	µA
			Auto					–20	+20	µA
I_{OZ}	Output Leakage Current	GND ≤ V_I ≤ V_{CC}, Output Disabled	Com'l/Ind'l	–1	+1	–1	+1	–1	+1	µA
			Auto					–20	+20	µA
I_{CC}	V_{CC} Operating Supply Current	V_{CC} = Max., I_{OUT} = 0 mA, f = f_{MAX} = $1/t_{RC}$	Com'l/Ind'l		90		85		80	mA
			Auto						85	mA
I_{SB1}	Automatic CE Power-down Current —TTL Inputs	Max. V_{CC}, $\overline{CE}$ ≥ V_{IH} V_{IN} ≥ V_{IH} or V_{IN} ≤ V_{IL}, f = f_{MAX}	Com'l/Ind'l		15		15		15	mA
			Auto						20	mA
I_{SB2}	Automatic CE Power-down Current —CMOS Inputs	Max. V_{CC}, $\overline{CE}$ ≥ V_{CC} – 0.3V, V_{IN} ≥ V_{CC} – 0.3V, or V_{IN} ≤ 0.3V, f = 0	Com'l/Ind'l		5		5		5	mA
			Auto						10	mA

Capacitance[3]

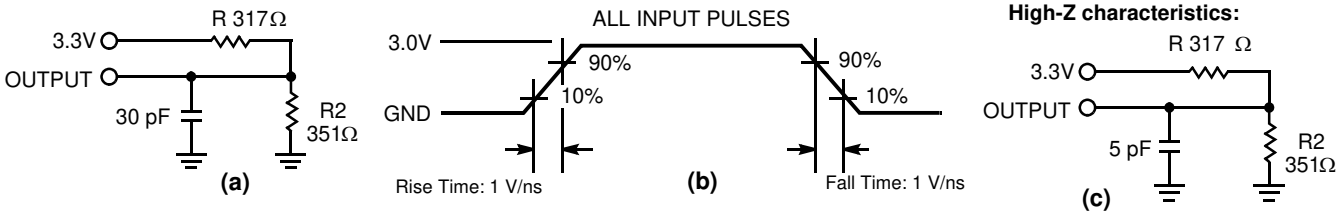
Parameter	Description	Test Conditions	Max.	Unit
C_{IN}	Input Capacitance	T_A = 25°C, f = 1 MHz, V_{CC} = 3.3V	8	pF
C_{OUT}	Output Capacitance		8	pF

Thermal Resistance[3]

Parameter	Description	Test Conditions	44-pin TSOP-II	Unit
Θ_{JA}	Thermal Resistance (Junction to Ambient)	Test conditions follow standard test methods and procedures for measuring thermal impedance, per EIA/JESD51.	76.92	°C/W
Θ_{JC}	Thermal Resistance (Junction to Case)		15.86	°C/W

Notes:
2. V_{IL} (min.) = –2.0V and V_{IH}(max) = V_{CC} + 0.5V for pulse durations of less than 20 ns.
3. Tested initially and after any design or process changes that may affect these parameters.

AC Test Loads and Waveforms[4]



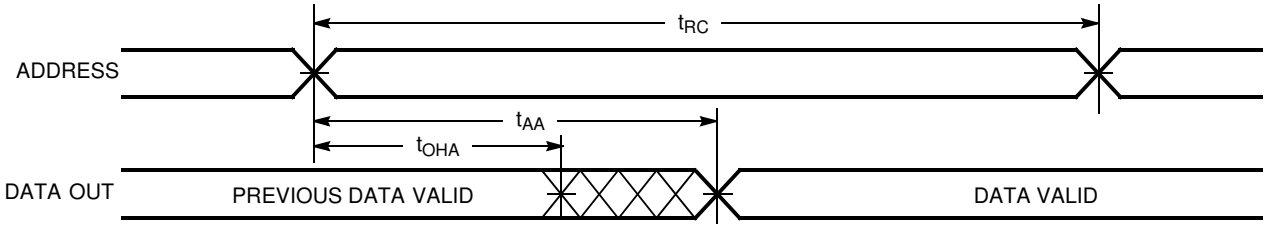
Switching Characteristics Over the Operating Range[4]

Parameter	Description	-10		-12		-15		Unit
		Min.	Max.	Min.	Max.	Min.	Max.	
Read Cycle								
t_{RC}	Read Cycle Time	10		12		15		ns
t_{AA}	Address to Data Valid		10		12		15	ns
t_{OHA}	Data Hold from Address Change	3		3		3		ns
t_{ACE}	$\overline{CE}$ LOW to Data Valid		10		12		15	ns
t_{DOE}	$\overline{OE}$ LOW to Data Valid		5		6		7	ns
t_{LZOE}	$\overline{OE}$ LOW to Low-Z[5]	0		0		0		ns
t_{HZOE}	$\overline{OE}$ HIGH to High-Z[5, 6]		5		6		7	ns
t_{LZCE}	$\overline{CE}$ LOW to Low-Z[5]	3		3		3		ns
t_{HZCE}	$\overline{CE}$ HIGH to High-Z[5, 6]		5		6		7	ns
t_{PU}[7]	$\overline{CE}$ LOW to Power-up	0		0		0		ns
t_{PD}[7]	$\overline{CE}$ HIGH to Power-down		10		12		15	ns
t_{DBE}	Byte Enable to Data Valid		5		6		7	ns
t_{LZBE}	Byte Enable to Low-Z	0		0		0		ns
t_{HZBE}	Byte Disable to High-Z		5		6		7	ns
Write Cycle[8]								
t_{WC}	Write Cycle Time	10		12		15		ns
t_{SCE}	$\overline{CE}$ LOW to Write End	8		9		10		ns
t_{AW}	Address Set-up to Write End	7		8		10		ns
t_{HA}	Address Hold from Write End	0		0		0		ns
t_{SA}	Address Set-up to Write Start	0		0		0		ns
t_{PWE}	$\overline{WE}$ Pulse Width	7		8		10		ns
t_{SD}	Data Set-up to Write End	5		6		8		ns
t_{HD}	Data Hold from Write End	0		0		0		ns
t_{LZWE}	$\overline{WE}$ HIGH to Low-Z[5]	3		3		3		ns
t_{HZWE}	$\overline{WE}$ LOW to High-Z[5, 6]		5		6		7	ns
t_{BW}	Byte Enable to End of Write	7		8		9		ns

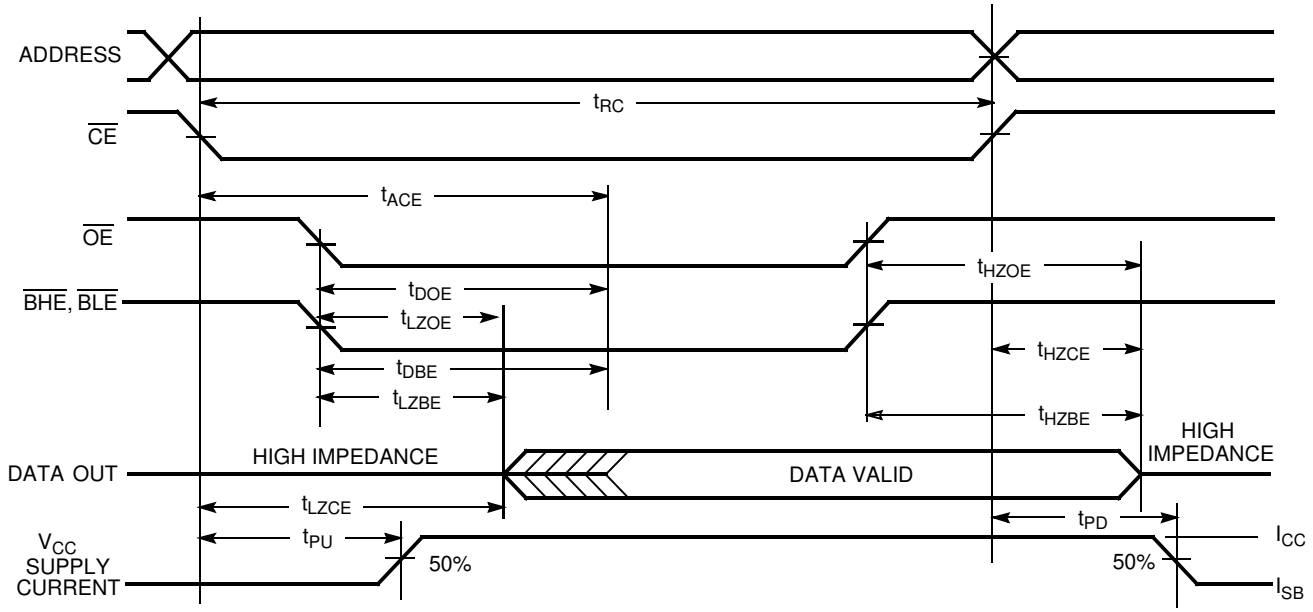
Notes:
4. Test conditions assume signal transition time of 3 ns or less, timing reference levels of 1.5V, input pulse levels of 0 to 3.0V.
5. At any given temperature and voltage condition, t_{HZCE} is less than t_{LZCE}, t_{HZOE} is less than t_{LZOE}, and t_{HZWE} is less than t_{LZWE} for any given device.
6. t_{HZOE}, t_{HZBE}, t_{HZCE}, and t_{HZWE} are specified with a load capacitance of 5 pF as in part (c) of AC Test Loads. Transition is measured ±500 mV from steady-state voltage.
7. This parameter is guaranteed by design and is not tested.
8. The internal Write time of the memory is defined by the overlap of $\overline{CE}$ LOW, $\overline{WE}$ LOW and $\overline{BHE}$/$\overline{BLE}$ LOW. $\overline{CE}$, $\overline{WE}$ and $\overline{BHE}$/$\overline{BLE}$ must be LOW to initiate a Write, and the transition of these signals can terminate the Write. The input data set-up and hold timing should be referenced to the leading edge of the signal that terminates the Write.

Switching Waveforms

Read Cycle No. 1[9, 10]



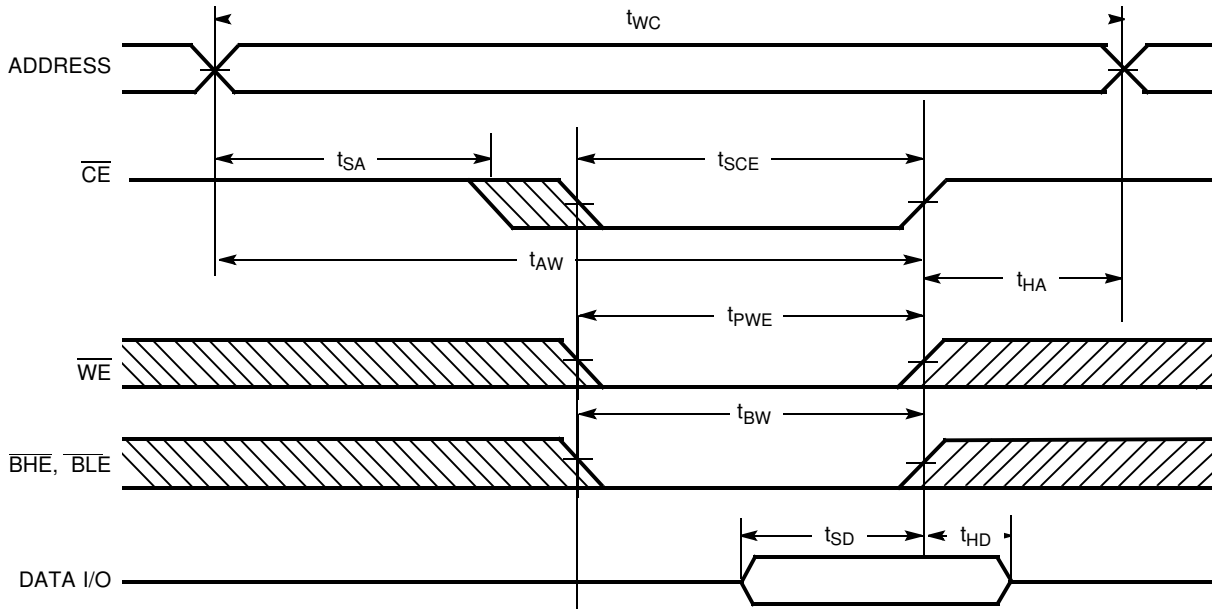
Read Cycle No. 2 ($\overline{OE}$ Controlled)[10, 11]



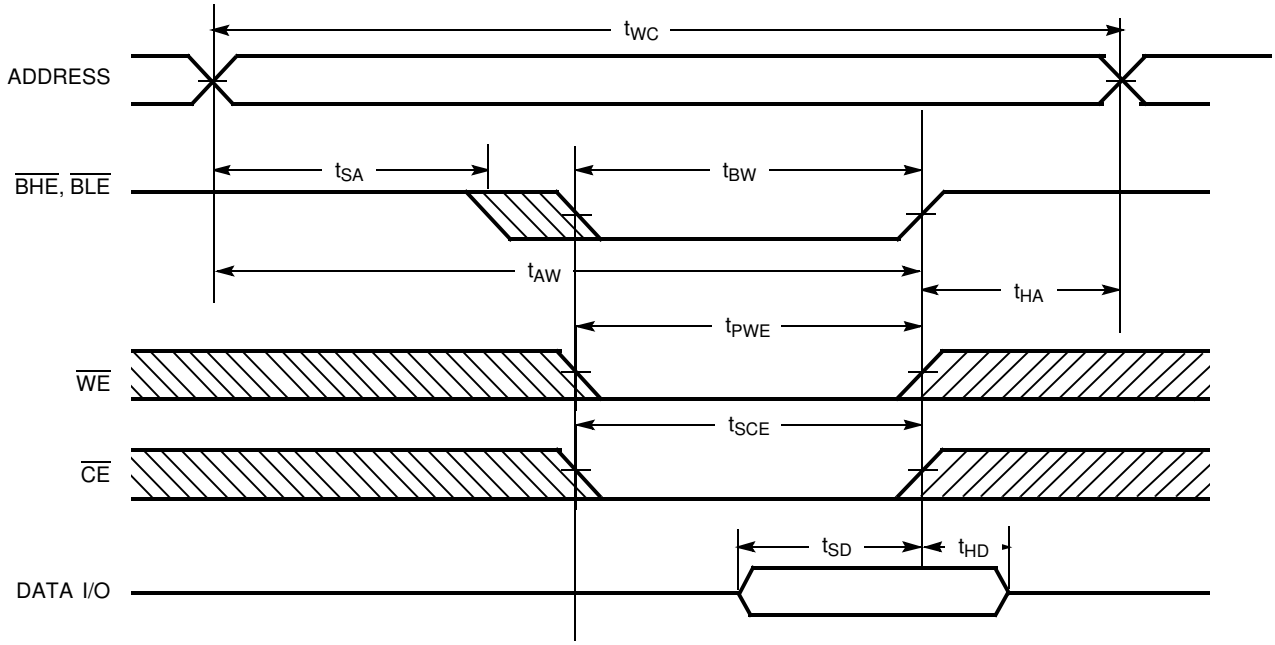
Notes:
9. Device is continuously selected. $\overline{OE}$, $\overline{CE}$, $\overline{BHE}$ and/or $\overline{BHE}$ = V_{IL}.
10. $\overline{WE}$ is HIGH for Read cycle.
11. Address valid prior to or coincident with $\overline{CE}$ transition LOW.

Switching Waveforms (continued)

Write Cycle No. 1 ($\overline{CE}$ Controlled)[12, 13]



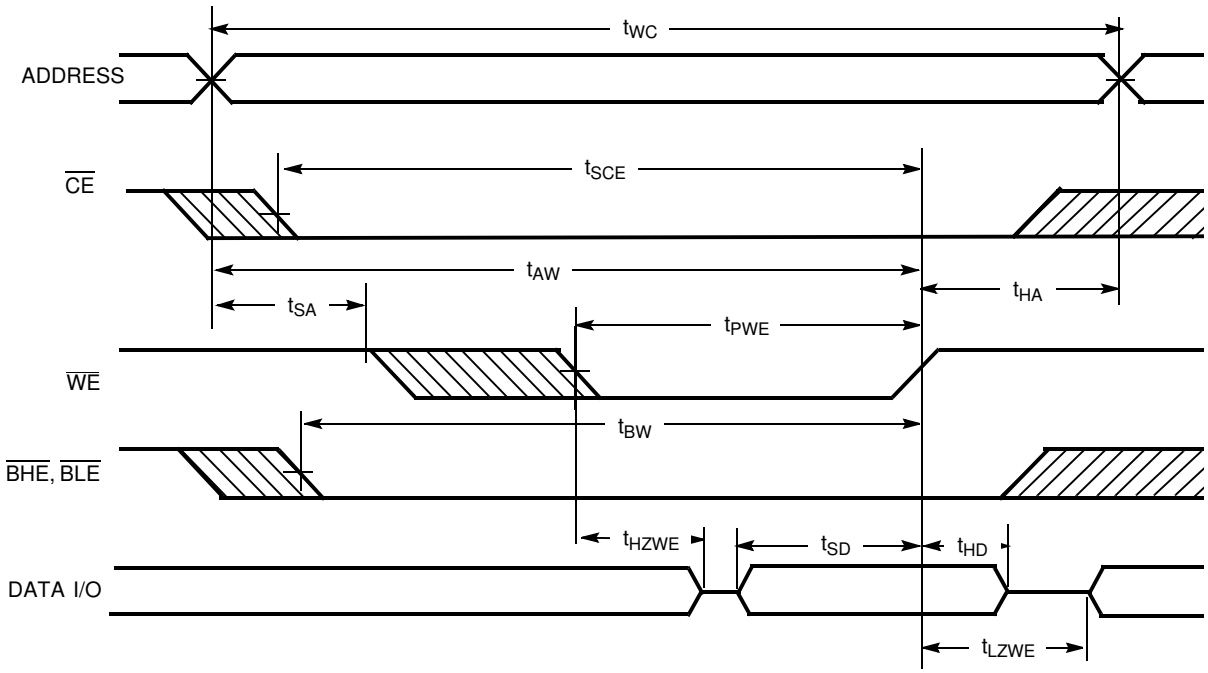
Write Cycle No. 2 ($\overline{BLE}$ or $\overline{BHE}$ Controlled)



Notes:
12. Data I/O is high impedance if $\overline{OE}$ or $\overline{BHE}$ and/or $\overline{BLE}$ = V_{IH}.
13. If $\overline{CE}$ goes HIGH simultaneously with $\overline{WE}$ going HIGH, the output remains in a high-impedance state.

Switching Waveforms (continued)

Write Cycle No. 3 ($\overline{WE}$ Controlled, $\overline{OE}$ LOW)



Truth Table

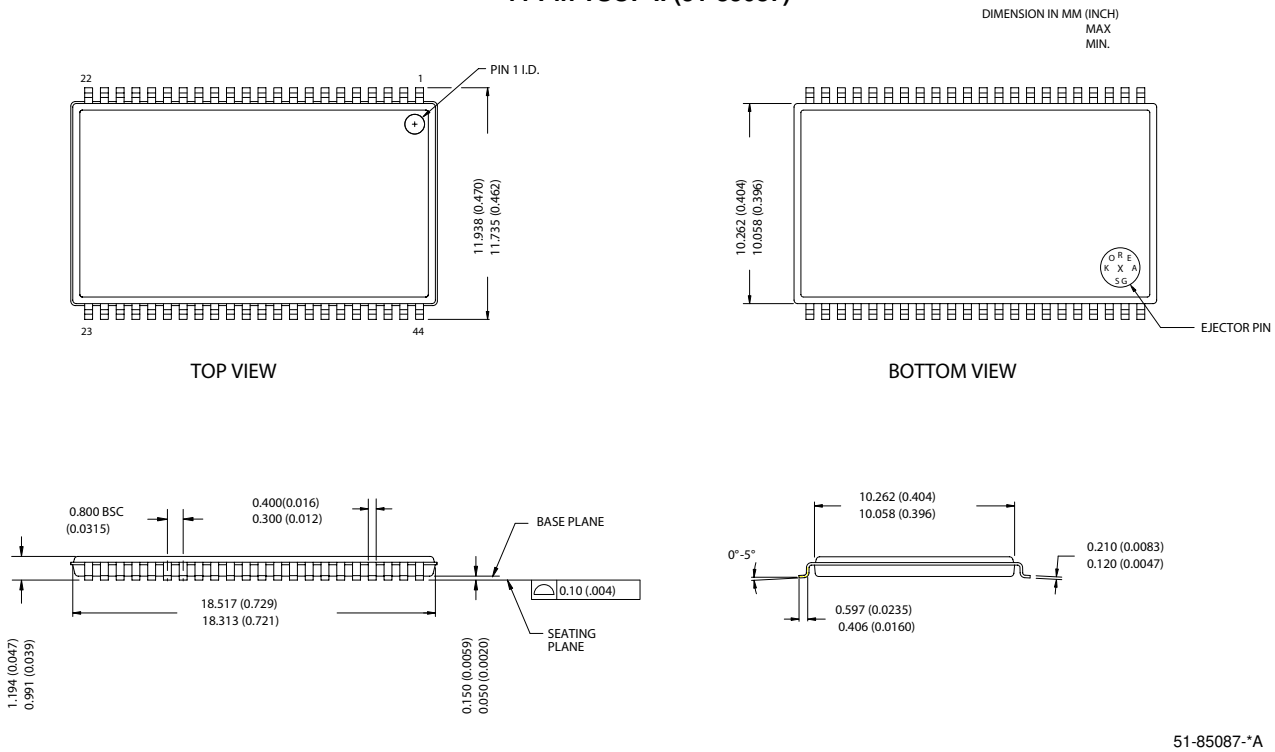
$\overline{CE}$	$\overline{OE}$	$\overline{WE}$	$\overline{BLE}$	$\overline{BHE}$	$I/O_1–I/O_8$	$I/O_9–I/O_{16}$	Mode	Power
H	X	X	X	X	High-Z	High-Z	Power-down	Standby (I_{SB})
L	L	H	L	L	Data Out	Data Out	Read—All bits	Active (I_{CC})
			L	H	Data Out	High-Z	Read—Lower bits only	Active (I_{CC})
			H	L	High-Z	Data Out	Read—Upper bits only	Active (I_{CC})
L	X	L	L	L	Data In	Data In	Write—All bits	Active (I_{CC})
			L	H	Data In	High-Z	Write—Lower bits only	Active (I_{CC})
			H	L	High-Z	Data In	Write—Upper bits only	Active (I_{CC})
L	H	H	X	X	High-Z	High-Z	Selected, Outputs Disabled	Active (I_{CC})
L	X	X	H	H	High-Z	High-Z	Selected, Outputs Disabled	Active (I_{CC})

Ordering Information

Speed (ns)	Ordering Code	Package Diagram	Package Type	Operating Range
10	CY7C1020CV33-10ZC	51-85087	44-pin TSOP Type II	Commercial
	CY7C1020CV33-10ZXC		44-pin TSOP Type II (Pb-Free)	
12	CY7C1020CV33-12ZC		44-pin TSOP Type II	Commercial
15	CY7C1020CV33-15ZC		44-pin TSOP Type II	Commercial
	CY7C1020CV33-15ZE		44-pin TSOP Type II	Automotive
	CY7C1020CV33-15ZSXE		44-pin TSOP Type II (Pb-Free)	

Package Diagrams

44-Pin TSOP II (51-85087)



Document History Page

Document Title: CY7C1020CV33 512K (32K x 16) Static RAM Document Number: 38-05133				
REV.	**ECN NO.**	**Issue Date**	**Orig. of Change**	**Description of Change**
**	109428	12/16/01	HGK	New Data Sheet
*A	115045	05/30/02	HGK	I_{CC} and I_{SB1} data modified
*B	117615	08/14/02	DFP	Pin 1= NC Pin 18 = A4; remove SOJ package option; remove 8ns option.
*C	262949	See ECN	RKF	Added Automotive Specs to Data sheet
*D	334398	See ECN	SYT	Added Lead-Free Product Information
*E	493543	See ECN	NXR	Added note #1 on page #1 Changed the description of I_{IX} from Input Load Current to Input Leakage Current in DC Electrical Characteristics table Removed I_{OS} parameter from DC Electrical Characteristics table Updated Ordering Information Table